

Universal T_c depression by irradiation defects in underdoped and overdoped cuprates

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Abstract

We report on a study of the influence of defects introduced in the CuO_2 planes of cuprates in a wide range of hole dopings n . T_c and electrical resistivity $\rho(T)$ measurements have been performed on electron irradiated $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ and $\text{Tl}_2\text{Ba}_2\text{CuO}_{6+x}$ single crystals. A universal scaling between the decrease in T_c and $\Delta\rho_{2D} \times n$, where $\Delta\rho_{2D}$ is the increase of the 2D-resistance induced by the defects, is found for all the samples investigated here. This demonstrates that n is the relevant parameter to describe the transport properties all over the phase diagram, in contradiction with a recent suggestion of a change in the number of carriers from n to $1 - n$ at the optimal doping. Moreover, the analysis of our data suggests that strong scattering persists on the overdoped side.

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It is well established that defects introduced in the CuO_2 planes of cuprates alter very effectively the properties of these materials in both their normal and superconducting states. In particular, the large T_c depression induced by Zn, a "non magnetic" scatterer, has been extensively studied¹⁻⁸. NMR and susceptibility measurements^{2,3,8} in Zn substituted YBCO samples have shown that Zn induces localized moments on neighbouring Cu sites. The size of these moments is tightly related to the hole doping, decreasing from $S \sim 1/2$ in underdoped samples to a very small value in optimally doped ones. Concerning transport properties, Fukuzumi et al⁶ have used Zn substitution in single crystals of YBCO and LaSrCuO to probe the evolution of the electronic state of high T_c cuprates with doping. Their results show a critical change in the normal state transport properties from the underdoped to optimal or overdoped regime, with the carrier density being identified with the density of doped holes in the former regime and with the density of electrons in the latter one. Nagaosa and Lee⁹ were able to account for these resistivity data in the framework of spin-charge separation theory. They proposed that the crossover in Zn induced residual resistivity increases should be due to a Kondo screening effect - screening of localized spins by conduction electron spins - which increases as the hole concentration increases and the local moment disappears.

Electron irradiation is another practical way to introduce in-plane defects in a controllable manner in high- T_c cuprates¹⁰⁻¹². More precisely, it has been previously shown in $\text{YBCO}_{7-\delta}$ that the irradiation defects relevant to explain the T_c decrease are related to oxygen and copper displacements in the CuO_2 planes. They induce a T_c depression quantitatively similar to Zn substitution¹⁰. The great advantage of electron irradiation is to allow transport measurements on the same sample with an increasing concentration of in-plane defects ranging from 0 to several % without changing the hole doping.

In this paper, we present results of resistivity measurements on single crystals of optimally and under-doped $\text{YBCO}_{7-\delta}$ and optimally and over-doped $\text{Tl}_2\text{Ba}_2\text{CuO}_{6+\delta}$ (Tl-2201) irradiated at low temperatures by 2.5 MeV electrons. This allows us to study the interplay

between in-plane defects and hole doping for a wide range of hole dopings. The remarkable result of this paper is to show that the relevant parameter to describe the changes in T_c and resistivity induced by in-plane defects is the concentration of doped holes, in contradiction with the analysis proposed in ref.6 and 9.

Single crystals of $\text{YBCO}_{7-\delta}$ were grown using the standard flux method as described elsewhere¹³. Some optimally doped crystals were subsequently annealed in air at different temperatures and quenched at room temperature to adjust their oxygen content. The evaluation of oxygen content in our crystals was made by comparing T_c values - taken as the middle of the superconducting transition- with published data¹⁴. Three different crystals were studied with δ values of 0.07, 0.2 and 0.4.

Tetragonal single crystals of $\text{Tl}_2\text{Ba}_2\text{CuO}_{6+\delta}$ were grown using a Cu-rich flux. Good electrical contacts are made by evaporating gold pads onto the as-grown samples. Furthermore, the crystals are annealed using various combinations of annealing temperature, atmosphere and time in order to obtain T_c values ranging from $\sim 2\text{K}$ to 83K ¹⁵. Four different crystals with T_c values of 80K, 54K, 33K and 31K have been used.

The electron irradiations were performed in the low temperature facility of the Van de Graaff electron accelerator at the LSI. During irradiation, the samples are immersed in liquid H_2 (21K) and the irradiation flux is limited to $2 \times 10^{14} \text{ e}^-/\text{cm}^2 \text{ s}$ in order to avoid heating of the samples. In-situ resistivity measurements have been performed between 20K and 300K.

Figures 1-a and 1-b show the temperature dependence of the in-plane resistivity ρ_{ab} for two single crystals of $\text{YBCO}_{7-\delta}$ with $\delta \sim 0.07$ and ~ 0.4 irradiated at 20K in the same run and annealed up to 300K for increasing electron fluences. One observes the same tendencies as usually found when defects are introduced into CuO_2 planes : T_c shifts downwards and the absolute value of the resistivity increases. For both optimal and underdoped compounds, the $\rho(T)$ curves are perfectly parallel showing that the irradiation defects induce a temperature-independent contribution to resistivity, i.e. Matthiessen's rule is very well verified. This also indirectly confirms that the hole doping is not modified under irradiation in agreement with Hall effect data on electron irradiated YBCO_7 ¹⁰. Therefore one can determine the increase of

residual resistivity $\Delta\rho$ due to in-plane defects with high accuracy as the vertical shift of the $\rho(T)$ curves. In underdoped crystals we can note that defects do not affect the characteristic temperature below which the pseudo gap starts to open as already observed^{2,4,12}. Moreover a metal-insulator transition is visible once resistivity values are around $300\mu\Omega\cdot\text{cm}$. We have also observed this transition in optimally doped YBCO crystals at about the same resistivity value but for much higher electron fluences¹⁶.

Intermediate measurements have been carried out without warming the samples above 100K. In such conditions we have previously shown the absence of defect annealing¹⁰. Very good linear dependences of the residual resistivity and the critical temperature versus electron fluences are found (fig.2). Similarly to the case of Zn substitution the decrease rate of T_c is faster on the underdoped side, increasing by a factor ~ 2 from O_7 to $O_{6.6}$ as reported in the inset of fig. 2.

In the case of YBCO₇, the threshold energies necessary to displace oxygen and copper atoms have been previously determined to be equal respectively to 10 and 15 eV¹⁰. The number of defects created per CuO₂ plane is $n_d^i = \sigma_d^i \varphi t$ where σ_d^i is the cross-section for displacing the atom i from its site and φt is the electron fluence. Calculations of σ_d^i ¹⁷ lead to a total number of displaced O and Cu atoms per CuO₂ plane $n_d \simeq 3.7 \times 10^{-3}$ for an electron fluence of 10^{19} e/cm². Even if this absolute value of n_d is not very accurate, one does not expect a variation with the oxygen content. This allows the precise comparison between the three different crystals studied here which is illustrated in figure 2. The rate of increase of the 2D-resistivity $\Delta\rho_{2D}$ increases from 0.6 to 1.9 k Ω /%defects with decreasing oxygen content from O_7 to $O_{6.6}$. To a first approximation we can consider that defects related to oxygen and copper displacements behave as identical scatterers¹⁸. Given the analogy emphasized above between irradiation defects and Zn substitution, it is tempting to compare our results for $\Delta\rho_{2D}$ to those found for Zn substitution. In YBCO_{6.6}⁶, $\Delta\rho_{2D}$ has also been determined from the parallel shift of the $\rho(T)$ curves. The obtained values of $\Delta\rho_{2D}/n_d$ are similar for Zn and irradiation defects. However, in YBCO₇ raw data reported in ref. 1 and 6 display an increase of the slope of the $\rho(T)$ curves with Zn substitution in contrast with our results

(see fig. 1-a). This could indicate that the Zn impurities introduce a temperature-dependent contribution to resistivity. In view of our experiment, this explanation seems unlikely and we rather think that this apparent breakdown of Matthiessen's rule signals a difference in hole doping between the pure and Zn substituted single crystals used by Fukuzumi et al⁶. As a consequence the analysis in ref. 6 in which $\Delta\rho_{2D}$ is determined as the 0K intercept of the T-linear part of $\rho(T)$ seems to us questionable.

If we assume as is usually done that the contribution of the s-wave channel dominates the scattering processes, the increase in ρ_{2D} can be written as

$$\Delta\rho_{2D} = \frac{4\hbar}{e^2} \frac{n_d}{n} \sin^2 \delta, \quad (1)$$

where δ is the scattering phase shift and n the carrier concentration. We have plotted in fig. 2 the values of $\Delta\rho_{2D}$ obtained in the unitarity limit ($\delta = \pi/2$) assuming that the carriers are the doped holes (with concentration x), that is $n = x$. We find that the lower the hole doping, the closer the experimental data with these unitarity limit estimates. Here we have taken x to be equal to 0.16, 0.12 and 0.09 respectively as the oxygen content decreases, using the relationship between T_c / T_{c0} and n proposed by Tallon et al²¹. These values are somewhat low compared to those usually assumed in the literature. Nevertheless, even with a value as high as $x = 0.23$ taken by Fukuzumi et al.⁶, our experimental result for YBCO₇ cannot be accounted for by using equation (1) with $n = 1 - x$ as proposed in ref.6 and 9 for Zn substituted crystals. One can see in fig.2 that our data lie well above the straight line obtained in this limit. As discussed above, the different conclusion in the case of Zn mainly arises from the difficulty encountered in ref.6 to determine the increase of residual resistivity.

Contrary to the case of YBCO, the response of Tl-2201 crystals to low temperature irradiation strongly depends on the doping level of the samples. The optimally doped crystals behave similarly to YBCO₇ : defects introduced at 20K are stable up to ~ 130 K and the resistivity above T_c exhibits a linear T dependence obeying Matthiessen's rule. However in overdoped crystals, irradiation at 20K induces a very fast decrease of T_c which the major

part is recovered after warming up the samples to 80K. Meanwhile, the irradiation induced increase of the normal state resistivity exhibits no thermal recovery. We think that this might be associated with a change of hole doping induced by oxygen displacements in the charge reservoir planes which are reversible after annealing above 80K. A detailed analysis of these effects will be reported elsewhere²⁰. Nevertheless after systematic annealing at 300K, one can see in figure 1-c that Matthiessen's rule is also very well verified for the most overdoped Tl-2201 crystal studied here. This is for us the indication that the residual defects remaining in the samples after this thermal treatment do not modify the hole doping. One can therefore conclude that the prime cause of T_c suppression after annealing at 300K is again due to the presence of defects in the CuO_2 planes. As for YBCO, the increase of $\Delta\rho$ due to these defects can be determined very precisely by the parallel shift of the $\rho(T)$ curves.

In this condition the actual value of n_d in the CuO_2 planes cannot be estimated reliably. However in order to compare the effect of irradiation in Tl-2201 and YBCO we have plotted in figure 3 the decreases in T_c , ΔT_c , as a function of $\Delta\rho_{2D}$ (a) and $\Delta\rho_{2D} \times n$ (b) with $n = x$ for all the samples studied here. We have used the same approach as described above to estimate the hole doping in Tl-2201²², which leads to $x = 0.16, 0.22$ and 0.25 for the optimally doped samples and for the overdoped ones with initial T_c of 54 and 31K respectively. Data obtained on the crystal with initial T_c of 33K give similar results as the one with $T_c=31\text{K}$ and has not been reported in fig.3. The striking result displayed in fig.3b is that, irrespective of the compound or of the hole doping, the data are located on the same pair-breaking curve. It is worth mentioning that such a scaling is also followed by single crystals of Bi-2212²³ and lightly underdoped single crystals of Hg-1223²⁴ irradiated in the same conditions.

This universal scaling strongly suggests that ΔT_c is due to impurity scattering in a d-wave superconductor as first suggested by Radtke et al²⁵. It is then given by the standard Abrikosov Gork'ov formula which for small n_d is written as

$$\Delta T_c = -\frac{\pi}{4k_B}\Gamma_n, \quad (2)$$

where $\Gamma_n = \frac{n_d}{\pi N(E_F)} \sin^2 \delta$ is the scattering rate in the normal state and $N(E_F)$ the density of states at the Fermi level.^{26,27} With a cylindrical Fermi surface, equation (2) transforms into :

$$\Delta T_c = -\frac{\pi e^2 \hbar}{8k_B m^*} \Delta \rho_{2D} \times n. \quad (3)$$

As comparable values of the effective mass m^* are found for YBCO and Tl-2201²⁹, our experimental results give strong support to eq.(3) and to a d-wave symmetry of the pairing state all over the phase diagram. It is worth noting here that an analysis in terms of anisotropic s-wave superconductors would lead to a similar expression as eq.(3) with the degree of anisotropy χ ($0 \leq \chi \leq 1$) as a proportionality coefficient in eq.(3)^{12,28}. Such an analysis would be unlikely as this parameter χ can hardly be the same for the two compounds studied here whatever their hole dopings. Moreover the correlation displayed in fig.3 is for us the clear indication that x is the relevant parameter to describe transport properties in the cuprates. We have also plotted in this figure the data of ref.6 on Zn substituted YBCO and LaSrCuO single crystals. To take into account our criticism of the determination of $\Delta \rho$ in the case of YBCO₇, we have estimated the residual resistivity from the data at 150K. One can see that the corresponding data for underdoped and optimally doped YBCO are consistent with the pair-breaking curve for irradiation defects. Such a result does not apply for the La_{1-x}Sr_xCuO₄ system. One explanation can be found in the observation that the increase in resistivity due to Zn substitution strongly depends on the initial state of the samples as recently shown for La_{0.75} Sr_{0.15}CuO₄ films³⁰. On the other hand, several experiments such as thermopower or NMR measurements^{22,31} have shown that this system exhibits singular properties which could indicate that it is not a generic compound for the cuprates.

Finally let us address the question of the evolution of $\sin^2 \delta$ with doping. The scaling displayed in fig. 3b indicates that ΔT_c per in-plane defect is proportional to $\sin^2 \delta$. This is quite compatible with our analysis of $\Delta \rho_{2D}$ shown in fig.2. Indeed the decrease of $\Delta T_c/n_d$ at increasing doping can be correlated to a decrease of δ from the unitarity limit $\delta = \pi/2$. On the overdoped side we have no direct estimate of $\sin^2 \delta$. Studies of impurities substitution

in different overdoped cuprates have shown that $\Delta T_c/n_d$ decreases up to $n \sim 0,2$ and then remains constant^{32,7}. If such a behaviour applies for the Tl-2201 system, the correlation reported in fig. 3 suggests that the phase shift goes on decreasing in the overdoped region. Taking similar values of $\sin^2\delta$ for optimally doped YBCO and Tl-2201 leads to a crude estimate $\sin^2\delta \sim 0.4$ for $n \sim 0.25$ which suggests that strong resonant impurity scattering persists on the overdoped side. Although the origin of this resonant scattering with realistic potential strength is not clear at the present time, this indicates strong correlations in the host system as proposed on the basis of a t-J model³³.

In summary, the analysis of resistivity data in electron irradiated YBCO and the universal scaling found between ΔT_c and the pair-breaking parameter Γ_n show unambiguously that the number of doped holes is the relevant parameter to describe transport properties in cuprates from the underdoped to the overdoped regime. Moreover, the large estimated scattering phase shift suggests strong scattering, which could result from large enough electronic correlations even in the overdoped regime.

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FIGURES

FIG. 1. Temperature dependences of the in-plane resistivity in YBCO_7 (a), $\text{YBCO}_{6.6}$ (b) and overdoped Tl-2201 (c). The $\rho(T)$ curves have been recorded after systematic annealing at 300K. The two YBCO crystals have been irradiated in the same run with fluences of 0, 2.5, 3.8 and $6 \times 10^{19} \text{ e/cm}^2$ respectively for curves 0 to 3. In the case of overdoped Tl-2201, the electron fluences were 0, 0.8 and $3.4 \times 10^{19} \text{ e/cm}^2$. In the case of irradiated Tl-2201, the appearance of an anomalous $\rho(T)$ peak just above the transition probably results from a non-uniform current density distribution in this specific crystal¹⁹.

FIG. 2. Increase of the 2D resistance measured at 100K (without warming the samples above 100K) for the different $\text{YBCO}_{7-\delta}$ single crystals as a function of the electron fluence and the in-plane defect concentration n_d . The solid lines indicate the fit using eq.(1) in the unitarity limit with the indicated values for the carrier concentration n . Inset : Corresponding decreases of the critical temperature versus n_d .

FIG. 3. Decrease in the critical temperature ΔT_c as a function of : (1) the increase in 2D resistance $\Delta\rho_{2D}$ (measured at 100K) and (2) the quantity $\Delta\rho_{2D} \times n$ for the different samples studied ($\circ$ YBCO_7 , $\bullet$ $\text{YBCO}_{6.8}$, $\times$ $\text{YBCO}_{6.6}$, $\square$ optimally doped Tl-2201, $\boxplus$ and $\blacksquare$ overdoped Tl-2201 with initial T_c of 54 and 31K. The empty and closed diamonds are the results for Zn-substituted $\text{YBCO}_{7-\delta}$ crystals with $\delta = 0.07$ and 0.37 with resistivity data taken at 150K. The empty and closed triangles are for Zn-substituted $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$ with $x = 0.15$ and 0.2 with resistivity data taken at 50K⁶.

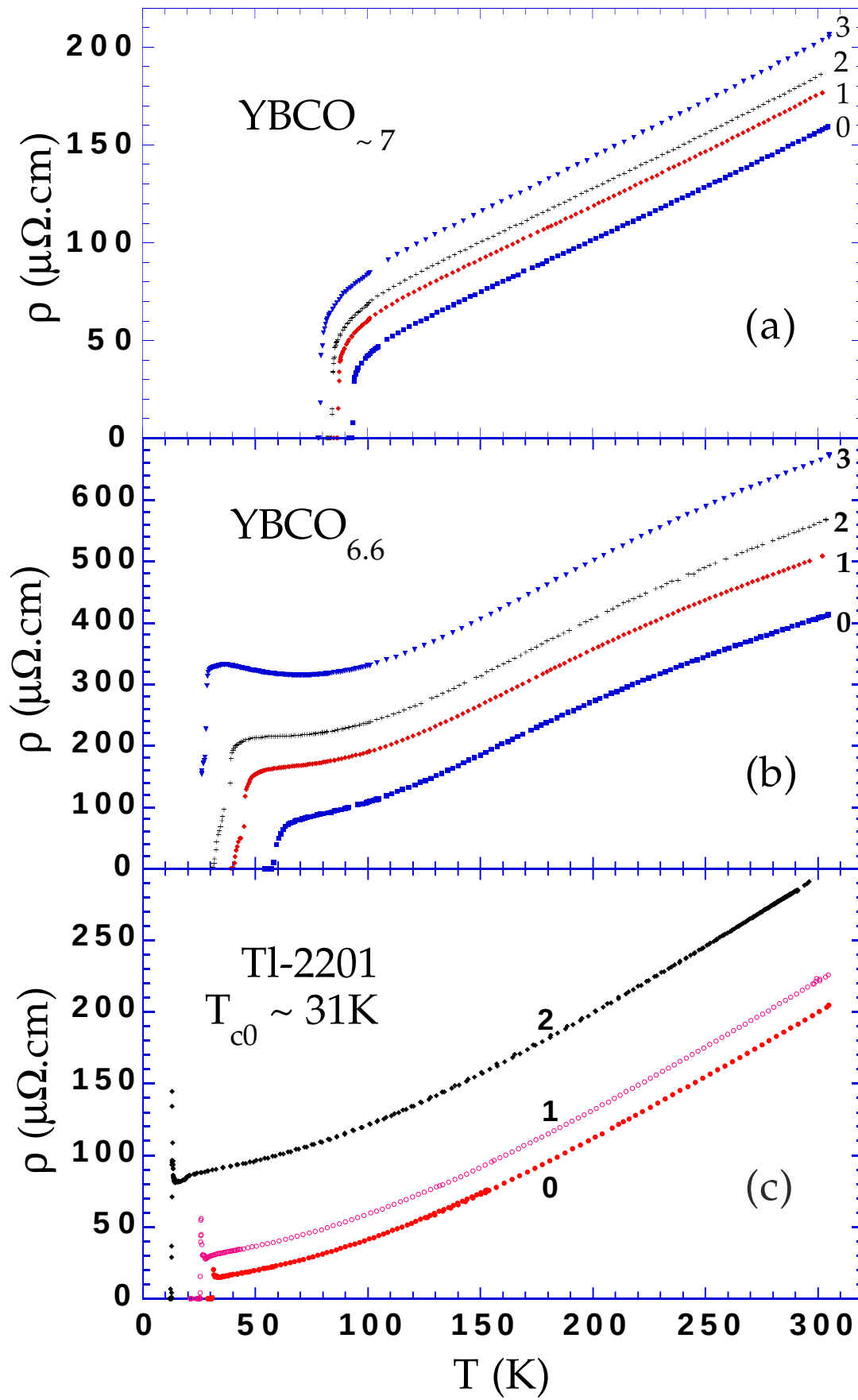


Figure 1 - F. Rullier-Albenque et al

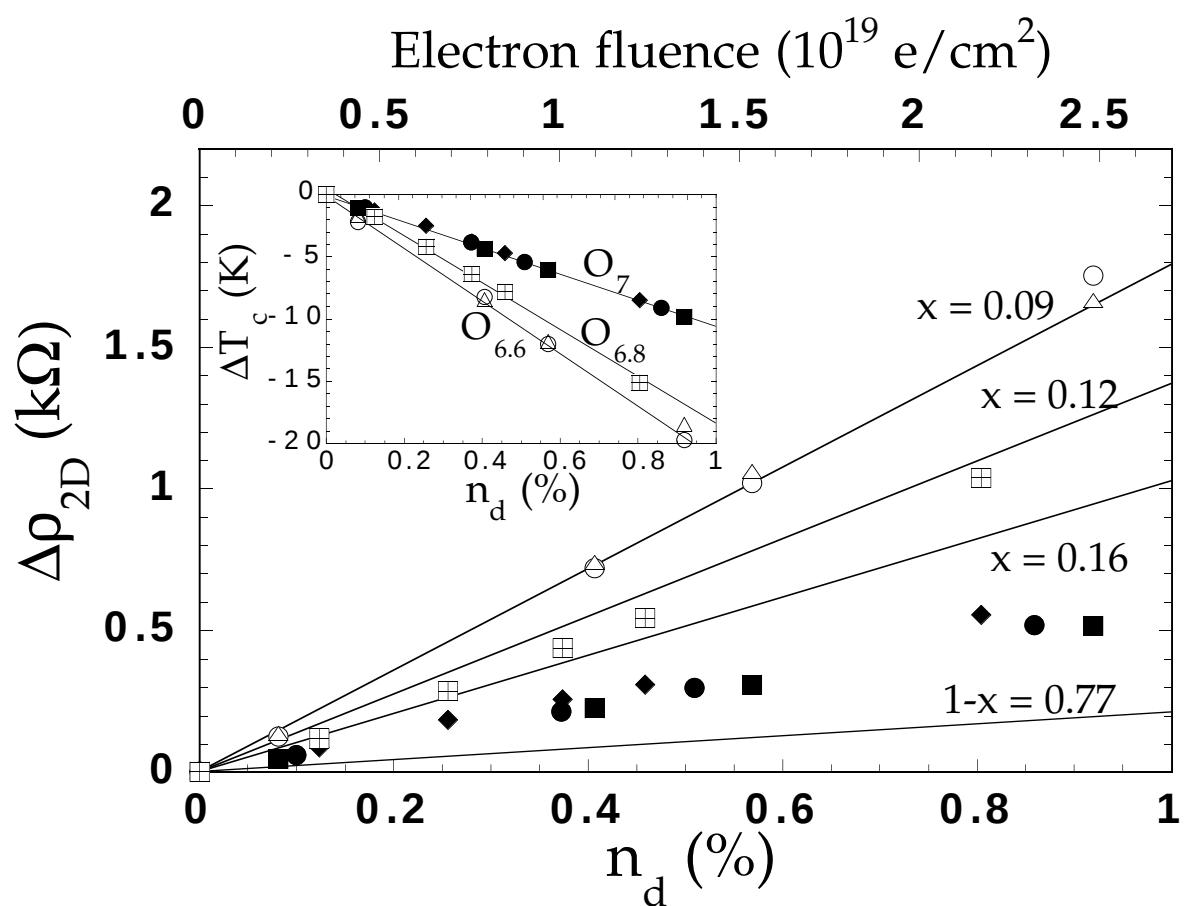


Figure 2 - F. Rullier-Albenque et al.

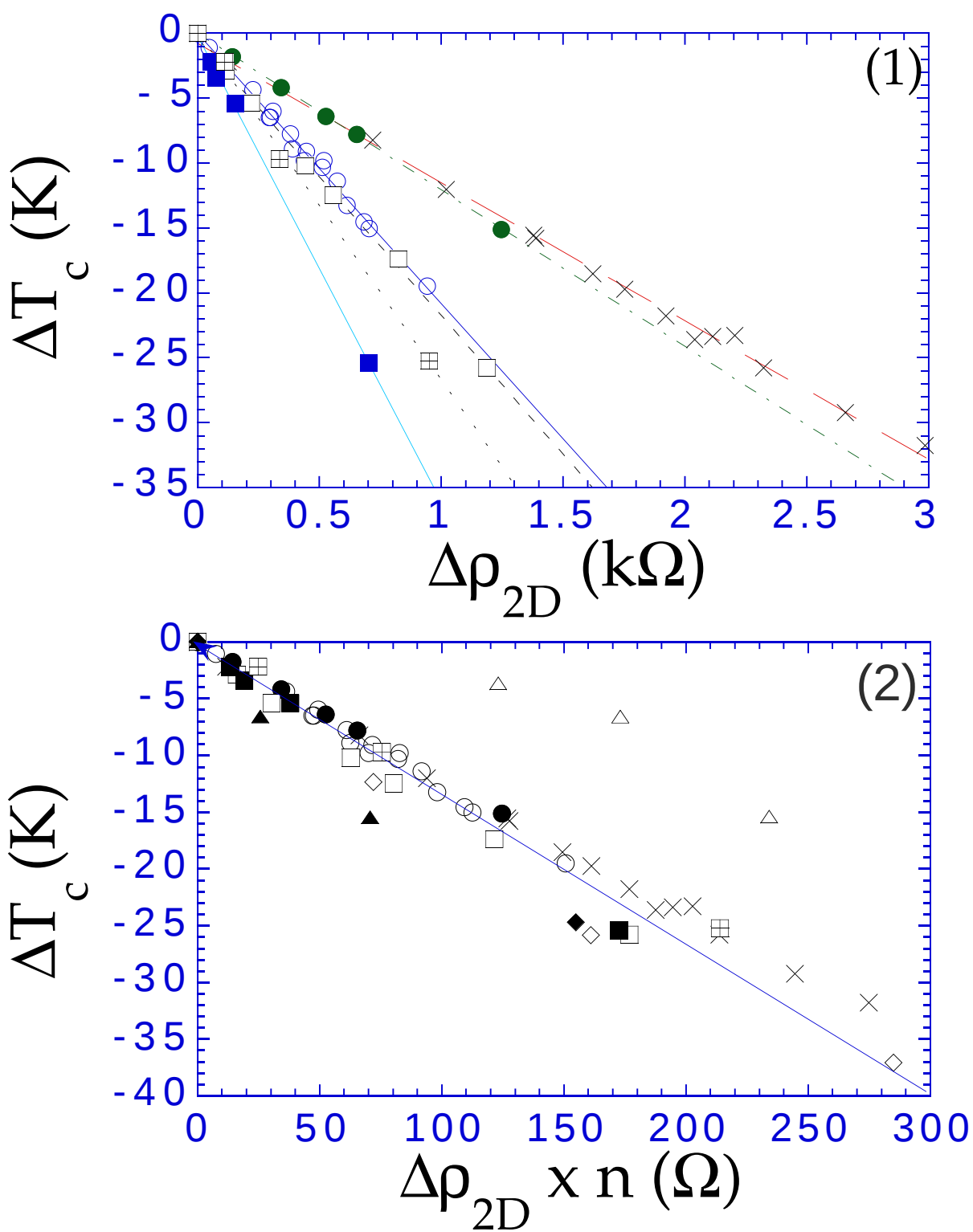


Figure 3 - F. Rullier-Albenque et al.